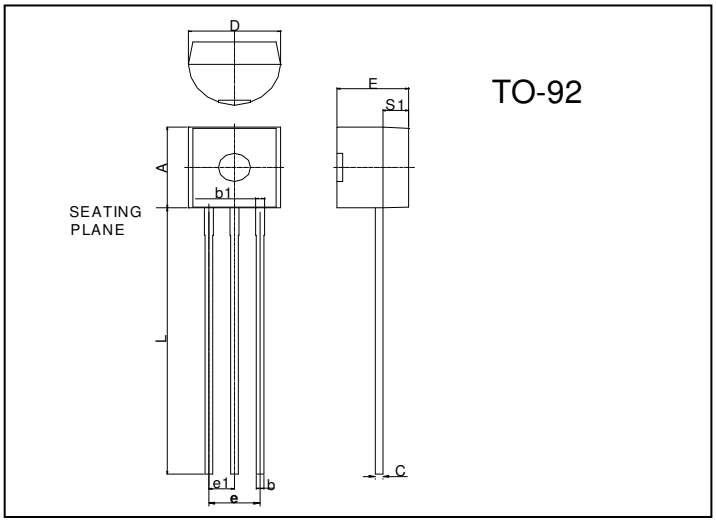
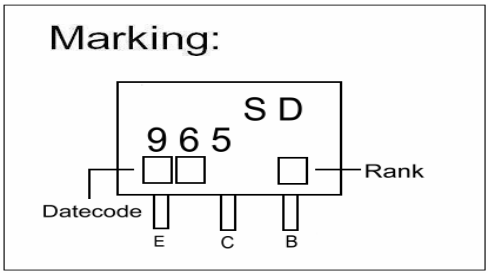
GSD965 NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GSD965 is designed for use as AF output amplifier and flash unit

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at Ta = 25℃

Collector to Base Voltage	BVCBO	40	V
Collector to Emitter Voltage	BVCEO	20	V
Emitter to Base Voltage	BVEBO	7.0	V
Collector Current (Continuous)	IC	5	A
Collector Current (Peak PT=10mS)	IC	8	A
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Total Power Dissipation at Ta = 25℃	PD	0.75	W

Characteristics at Ta = 25℃

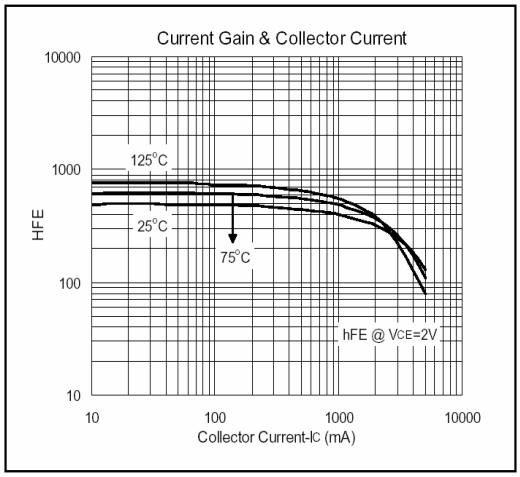
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	40	-	-	V	IC=100uA
BVCEO	20	-	-	V	IC=1mA
BVEBO	7	-	-	V	IE=10uA
ICBO	-	-	0.1	uA	VCB=60V
IEBO	-	-	0.1	uA	VEB=7V
*VCE(sat)	-	0.35	1	V	IC=3A, IB=0.1A
*hFE1	230	-	800		VCE=2V, IC=0.5A
*hFE2	150	-	-		VCE=2V, IC=2A
fT	-	150	-	MHz	VCE=6V, IE=50mA
Cob	-	-	50	pF	VCB=20V, f=1MHz

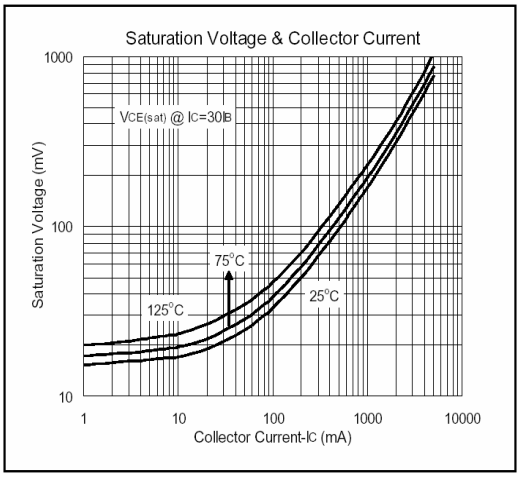
* Pulse Test: Pulse Width≦380us, Duty Cycle≦2%

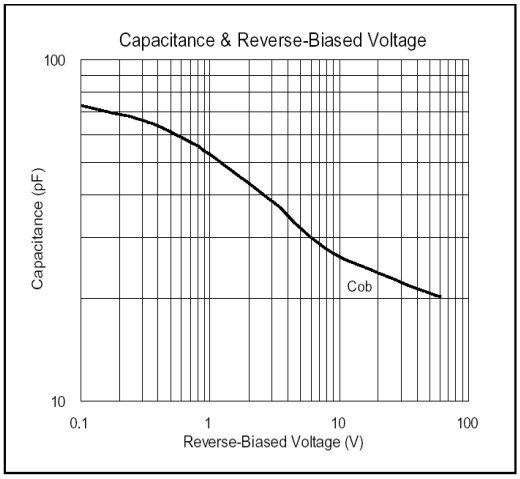
Classification Of hFE1

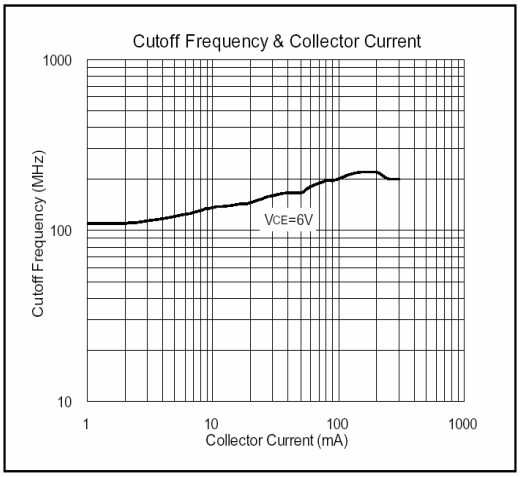
Rank	Q	R	S
Range	230-380	340-600	560-800

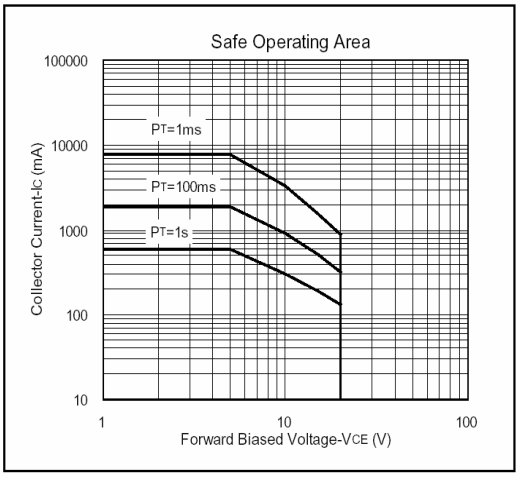
Characteristics Curve











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